(19) World Intellectual Property **Organization**

International Bureau





(43) International Publication Date 21 May 2004 (21.05.2004)

PCT

(10) International Publication Number WO 2004/042801 A3

(51) International Patent Classification⁷:

H01S 5/34

(21) International Application Number:

PCT/GB2003/004705

(22) International Filing Date: 30 October 2003 (30.10.2003)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

0225586.7

2 November 2002 (02.11.2002) GB

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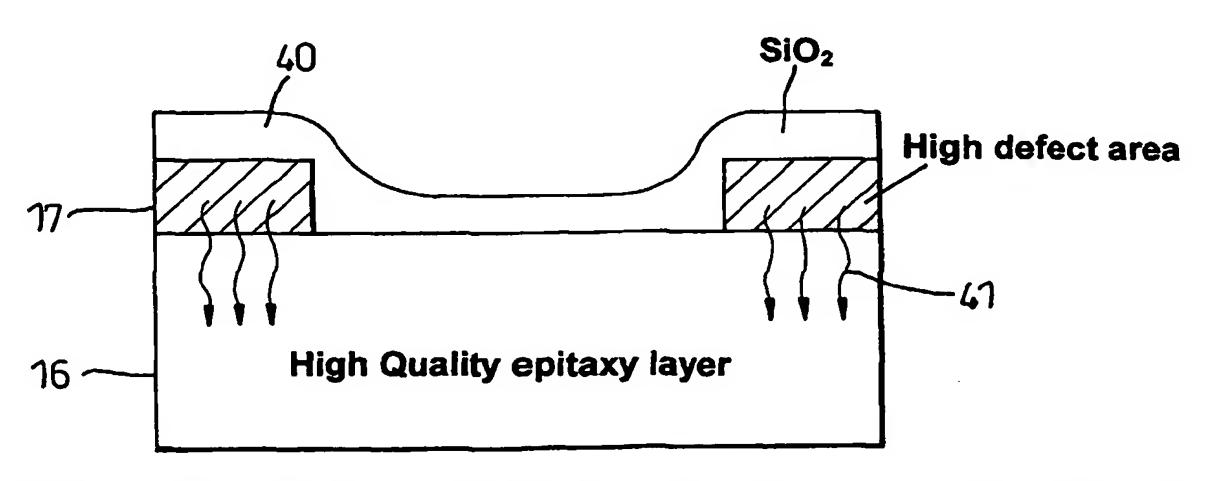
- (81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (regional): ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments
- (88) Date of publication of the international search report: 28 October 2004

(74) Agent: CHARIG, Raymond; Eric Potter Clarkson, Park For two-letter codes and other abbreviations, refer to the "Guid-View House, 58 The Ropewalk, Nottingham NG1 5DD ance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: QUANTUM WELL INTERMIXING IN SEMICONDUCTOR PHOTONIC DEVICES



(57) Abstract: A method for fabricating a semiconductor device in a semiconductor structure, provides enhanced quantum well intermixing in desired regions of the device by forming a first, relatively high quality, epitaxial layer on a substrate, the high quality layer including a quantum well; forming a second, relatively lower quality, epitaxial defect layer on top of the high quality layer; and thermally processing the structure to effect at least partial diffusion of the defects from the defect layer into the high quality layer in order to achieve quantum well intermixing in the structure. The use of an epitaxially grown defect layer on top of, or within, a high quality epitaxially grown device body enables quantum well intermixing techniques to be performed at lower temperatures and thereby improves device characteristics.

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According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols) IPC 7 H01L H01S

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

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Date of the actual completion of the international search	Date of mailing of the International search report
14 September 2004	23/09/2004
Name and mailing address of the ISA European Patent Office, P.B. 5818 Patentlaan 2 NL – 2280 HV Rijswijk Tel. (+31–70) 340–2040, Tx. 31 651 epo nl, Fax: (+31–70) 340–3016	Authorized officer Claessen, L

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